

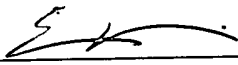
REMARKS

The Examiner's Office Action dated October 10, 2001 has been received and carefully reviewed. Claims 1-21 were pending in the present application, each of which is subject to a restriction requirement. By this Amendment, claims 1-3, 5-8, 10-13, 15-19, and 21 have been canceled. Claims 4, 9, 14, 20 have been amended. Claims 22-53 have been added. Accordingly, claims 4, 9, 14, 20, and 22-53 are pending, of which all, except claims 35-53, are independent. Specifically, among other amendments, Applicants have deleted the parenthetical notations at the end of each claim. These notations should not be used for purposes of analyzing the patentability or scope of the claims.

In response to the Election Requirement, Applicants provisionally elect to prosecute Group XII, i.e., claim 14 as herein amended. Claims 14 and 20 are generic. Claims 4, 9, and 22-53 are readable thereon. It is understood from the undersigned's January 3, 2002 interview with Examiner Ton that each pending claim will be prosecuted on the merits.

Consequently, in accordance with the provisions of 37 C.F.R. §1.141, Applicants respectfully reserve the right to prosecute claims directed to other species upon the allowance of a generic claim.

Respectfully submitted,


Eric J. Robinson
Registration No. 38,285

NIXON PEABODY LLP
8180 Greensboro Drive, Suite 800
McLean, VA 22102
(703) 790-9110

EJR/DLM/wks

VERSION OF AMENDED CLAIMS
SHOWING CHANGES MADE

4. (Amended) A device having at least one [liquid crystal] display panel, said [liquid crystal] display panel comprising:

a substrate having an insulating surface;

at least one thin film transistor formed over said substrate, said thin film transistor including at least a channel region, source and drain regions with said channel region therebetween, a gate insulating film adjacent to said channel region, and a gate electrode adjacent to said channel region with said gate insulating film interposed therebetween;

an interlayer insulating film covering said thin film transistor;

a lead electrode comprising aluminum formed [on] over said interlayer insulating film and electrically connected to one of the source or drain regions of said thin film transistor through a hole of said interlayer insulating film;

an organic resin film formed over the thin film transistor, said interlayer insulating film and said lead electrode to provide a leveled upper surface; and

a pixel electrode formed over said organic resin film, said pixel electrode being electrically connected to said thin film transistor via said lead electrode[,

wherein said channel region comprises crystal silicon and exhibits a peak of Raman spectra displaced from 522 cm^{-1} to the low frequency direction (1 + lead electrode comprising aluminum)].

9. (Amended) A television comprising:

a tuner for receiving television radio wave;

a [liquid crystal] display panel operationally connected to said tuner, said [liquid crystal] display panel comprising:

a substrate having an insulating surface;

at least one thin film transistor formed over said substrate, said thin film transistor including at least a channel region, source and drain regions with said channel region therebetween, a gate insulating film adjacent to said channel region, and a gate electrode adjacent to

said channel region with said gate insulating film interposed therebetween;

an interlayer insulating film covering said thin film transistor;

a lead electrode comprising aluminum formed [on] over said interlayer insulating film and electrically connected to one of the source or drain regions of said thin film transistor through a hole of said interlayer insulating film;

an organic resin film formed over the thin film transistor, said interlayer insulating film and said lead electrode to provide a leveled upper surface; and

a pixel electrode formed over said organic resin film, said pixel electrode being electrically connected to said thin film transistor via said lead electrode[,

wherein said channel region comprises crystal silicon and exhibits a peak of Raman spectra displaced from 522 cm⁻¹ to the low frequency direction (6 + lead electrode comprising aluminum)].

14. (Amended) A portable computer having a [liquid crystal] display panel, said [liquid crystal] display panel comprising:

a substrate having an insulating surface;

at least one thin film transistor formed over said substrate, said thin film transistor including at least a channel region, source and drain regions with said channel region therebetween, a gate insulating film adjacent to said channel region, and a gate electrode adjacent to said channel region with said gate insulating film interposed therebetween;

an interlayer insulating film covering said thin film transistor;

a lead electrode comprising aluminum formed [on] over said interlayer insulating film and electrically connected to one of the source or drain regions of said thin film transistor through a hole of said interlayer insulating film;

an organic resin film formed over the thin film transistor, said interlayer insulating film and said lead electrode to provide a leveled upper surface; and

a pixel electrode formed over said organic resin film, said pixel electrode being electrically connected to said thin film transistor via said lead electrode[,

wherein said channel region comprises crystal silicon and exhibits a peak of

Raman spectra displaced from 522 cm⁻¹ to the low frequency direction (11 + lead electrode comprising aluminum)].

20. (Amended) A device having at least one [flat panel] display device, said [flat panel] display device comprising:

a substrate having an insulating surface;

at least one thin film transistor formed over said substrate, said thin film transistor including at least a channel region, source and drain regions with said channel region therebetween, a gate insulating film adjacent to said channel region, and a gate electrode adjacent to said channel region with said gate insulating film interposed therebetween;

an interlayer insulating film covering said thin film transistor;

a lead electrode comprising aluminum formed [on] over said interlayer insulating film and electrically connected to one of the source or drain regions of said thin film transistor through a hole of said interlayer insulating film;

an organic resin film formed over the thin film transistor, said interlayer insulating film and said lead electrode to provide a leveled upper surface; and

a pixel electrode formed over said organic resin film, said pixel electrode being electrically connected to said thin film transistor via said lead electrode[,

wherein said channel region comprises crystal silicon and exhibits a peak of Raman spectra displaced from 522 cm⁻¹ to the low frequency direction (4- LCD)].